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DATE MAILED: 07/13/2006

PPLICATION NO.	f	ILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/766,148	•	01/27/2004	Yoshihide Senzaki	A-70028-2/MSS/TJH (463035	1972	
32940	7590	07/13/2006		EXAM	EXAMINER	
DORSEY	& WHIT	NEY LLP	CAO, PHAT X			
555 CALIF	ORNIA S'	TREET, SUITE 1000				
SUITE 1000				ART UNIT	PAPER NUMBER	
SAN FRAN	CISCO,	CA 94104		2814		

Please find below and/or attached an Office communication concerning this application or proceeding.

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		Ap	plication No.	Applicant(s)				
		10	766,148	SENZAKI, YOSH	IHIDE			
Office Action Summary			miner	Art Unit				
		Pha	at X. Cao	2814				
Period fo	The MAILING DATE of this commun r Reply	ication appears	on the cover sheet wi	th the correspondence a	ddress			
WHIC - Exter after - If NO - Failu Any r	CRTENED STATUTORY PERIOD F HEVER IS LONGER, FROM THE M sisions of time may be available under the provisions SIX (6) MONTHS from the mailing date of this comm period for reply is specified above, the maximum st re to reply within the set or extended period for reply eply received by the Office later than three months and patent term adjustment. See 37 CFR 1.704(b).	IAILING DATE of 37 CFR 1.136(a). nunication. atutory period will app will, by statute, cause	OF THIS COMMUNIC In no event, however, may a re by and will expire SIX (6) MON the application to become AB	CATION.  eply be timely filed  THS from the mailing date of this of the MANDONED (35 U.S.C. § 133).				
Status								
1)	Responsive to communication(s) file	ed on <i>02 May 2</i>	006.					
•	·	2b)⊠ This action						
-/-	Since this application is in condition	•—		ers, prosecution as to th	e merits is			
٠,١	closed in accordance with the practi		•	· •				
Dispositi	on of Claims	·	•					
-		annlication						
•	Claim(s) <u>1-12</u> is/are pending in the application.  4a) Of the above claim(s) is/are withdrawn from consideration.							
	Claim(s) is/are allowed.	William and it						
· · · · ·	Claim(s) <u>1-12</u> is/are rejected.							
·	Claim(s) is/are objected to.							
· ·	Claim(s) are subject to restrict	ction and/or ele	ction requirement.					
,	on Papers		·					
	•	- F						
•	The specification is objected to by the		d or h\C objected to	by the Everniner				
10)[_]	The drawing(s) filed on is/are							
	Applicant may not request that any obje				YED 4 404/d\			
44)	Replacement drawing sheet(s) including The oath or declaration is objected to							
11)[_]	The bath of declaration is objected to	o by the Examin	ier. Note the attached	Office Action of John P	10-132.			
Priority ι	ınder 35 U.S.C. § 119							
<ul> <li>12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).</li> <li>a) All b) Some * c) None of:</li> <li>1. Certified copies of the priority documents have been received.</li> <li>2. Certified copies of the priority documents have been received in Application No.</li> <li>3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).</li> <li>* See the attached detailed Office action for a list of the certified copies not received.</li> </ul>								
2) П Notic 3) П Infoл	t(s) e of References Cited (PTO-892) e of Draftsperson's Patent Drawing Review (F mation Disclosure Statement(s) (PTO-1449 or r No(s)/Mail Date		Paper No(s	Summary (PTO-413) s)/Mail Date nformal Patent Application (PT 	<sup>-</sup> O-152)			



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## **DETAILED ACTION**

1. The Request for Continued Examination filed on 5/2/06 is acknowledged.

## Claim Rejections - 35 USC § 103

- 2. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
  - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- Claims 1-12 are rejected under 35 U.S.C. 103(a) as being unpatentable over 3. Steigerwald et al (US. 6,479,404) in view of hegde et al (US. 6,383,873).

Regarding claims 1 and 12, Steigerwald discloses a multilayer gate dielectric film (column 1, lines 61-63) comprising: a first layer formed of Zirconium oxide material (column 7, lines 57-59 and column 8, lines 5-9) having a dielectric constant k and thickness t, the zirconium oxide material having the formula of M(x)O(y) (i.e., ZrO(2)); a second layer formed on top of the first layer, wherein the second layer is formed of zirconium silicate material (column 7, lines 57-59 and column 8, lines 5-9) having a dielectric constant lower than that of the first layer of zirconium oxide material.

Steigerwald does not disclose that the second layer has a thickness smaller than the thickness of the first layer.

However, Hegde (Fig. 5) teaches a multilayer gate dielectric film comprising: a first layer 106 formed of a metal oxide material (column 2, lines 24-34) and having a thickness of 20-80 angstroms (column 2, lines 62-65); and a second layer 108 of a metal silicate material containing metallic element (column 3, lines 21-27) and formed

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on the first layer 106, the second layer 108 having a thickness in the range of one to two atomic layers (column 4, lines 3-4). Accordingly, it would have been obvious to form the second layer having a thickness smaller than the thickness of the first layer because it is desirable to minimize the thickness of the second layer to maintain the high-k characteristics of the composite gate dielectric film, as taught by hegde (column 3, lines 64-66).

Regarding claims 2-3, Steigerwald further discloses that the first layer of metal oxide and the second layer of metal silicate having a dielectric constant of at least about 10 (column 2, lines 51-54).

Regarding claims 4, 6-7 and 9, Steigerwald further discloses that the first layer is ZrO(2) and the second layer is ZrSiO(4) (column 7, lines 57-59).

Regarding claims 5 and 8, Steigerwald further discloses that the metal oxide first layer and the metal silicate second layer include more than one metal element (column 2, lines 51-57).

Regarding claims 10-11, Hegde further teaches that a first layer 106 of metal oxide having a thickness in a range of about 20-80 angstroms (column 2, lines 62-65), and the second layer 108 of metal silicate having a thickness in the range of about one to two atomic layers (column 4, lines 3-4).

## Response to Arguments

4. Applicant's arguments with respect to the claimed invention have been considered but are moot in view of the new ground(s) of rejection. The new references are applied in the new ground of rejection.

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5. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Phat X. Cao whose telephone number is 571-272-1703. The examiner can normally be reached on M-F.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Wael Fahmy can be reached on 571-272-1705. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

PC

July 7, 2006

PHAT X. CAO PRIMARY EXAMINER